

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### Features

- Self-aligned planar Technology
- Improve switching performance

#### Applications

- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

#### Quick reference

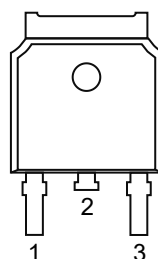
- $V_{DS} = 200V$
- $I_D = 18A$
- $R_{DS(ON)} < 150m\Omega @ V_{GS} = 10V$  (Type:120m $\Omega$ )

#### Pin Description

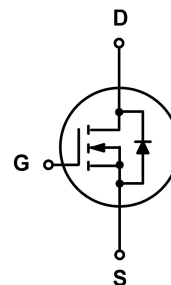
| Pin | Description |
|-----|-------------|
| 1   | Gate(G)     |
| 2   | Drain(D)    |
| 3   | Source(S)   |

#### Simplified Outline

#### Symbol



Top View  
TO-252



#### Package Marking and Ordering Information

| Product Name | Package | Marking         | Reel Size | Tape width | Quantity |
|--------------|---------|-----------------|-----------|------------|----------|
| KJ18N20K     | TO-252  | 18N20<br>XXXXYY | -         | -          | 2500     |

### 2. Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise noted)

| Symbol                            | Parameter                                        | Values   | Unit |
|-----------------------------------|--------------------------------------------------|----------|------|
| $V_{DS}$                          | Drain-Source Voltage ( $V_{GS}=0V$ )             | 200      | V    |
| $V_{GS}$                          | Gate-Source Voltage                              | $\pm 20$ | V    |
| $I_D$                             | Continuous Drain Current, $V_{GS}@10V$           | 18       | A    |
| $I_{DM}$                          | Pulsed Drain Current <sup>1</sup>                | 72       | A    |
| $E_{AS}$                          | Single Pulse Avalanche Energy <sup>2</sup>       | 340      | mJ   |
| $I_{AS}$                          | Avalanche Current <sup>1</sup>                   | 15       | A    |
| $E_{AR}$                          | Repetitive Avalanche Energy <sup>1</sup>         | 8.3      | mJ   |
| $P_D$                             | Power Dissipation @T <sub>C</sub> =25°C          | 104      | W    |
| T <sub>J</sub> , T <sub>STG</sub> | Operating Junction and Storage Temperature Range | -55~150  | °C   |
| R <sub>θJA</sub>                  | Thermal Resistance, Junction-to-Ambient          | 62.5     | °C/W |
| R <sub>θJC</sub>                  | Thermal Resistance Junction-Case                 | 1.2      | °C/W |

## 3. Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

| Symbol              | Parameter                                              | Test Conditions                                                  | Min. | Typ. | Max. | Unit |
|---------------------|--------------------------------------------------------|------------------------------------------------------------------|------|------|------|------|
| V <sub>DSS</sub>    | Drain-Source Breakdown Voltage                         | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA                       | 200  | 220  | -    | V    |
| I <sub>GSS</sub>    | Gate-body Leakage current                              | V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V                       | -    | -    | ±100 | nA   |
| I <sub>DSS</sub>    | Zero Gate Voltage Drain Current, T <sub>J</sub> =25°C  | V <sub>DS</sub> =200V, V <sub>GS</sub> =0V                       | -    | -    | 5    | μA   |
| I <sub>DSS</sub>    | Zero Gate Voltage Drain Current, T <sub>J</sub> =125°C | V <sub>DS</sub> =160V, V <sub>GS</sub> =0V                       | -    | -    | 100  |      |
| V <sub>GS(th)</sub> | Gate-Threshold Voltage                                 | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA         | 1.0  | 1.6  | 3.0  | V    |
| R <sub>DS(on)</sub> | Drain-Source on-Resistance <sup>3</sup>                | V <sub>GS</sub> =10V, I <sub>D</sub> =9A                         | -    | 120  | 150  | mΩ   |
| C <sub>iss</sub>    | Input Capacitance                                      | V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, Frequency=1MHz        | -    | 1318 | -    | pF   |
| C <sub>oss</sub>    | Output Capacitance                                     |                                                                  | -    | 180  | -    |      |
| C <sub>rss</sub>    | Reverse Transfer Capacitance                           |                                                                  | -    | 75   | -    |      |
| Q <sub>g</sub>      | Total Gate Charge                                      | V <sub>GS</sub> =10V, V <sub>DS</sub> =160V, I <sub>D</sub> =18A | -    | 41   | -    | nC   |
| Q <sub>gs</sub>     | Gate-Source Charge                                     |                                                                  | -    | 5.5  | -    |      |
| Q <sub>gd</sub>     | Gate-Drain Charge                                      |                                                                  | -    | 19.5 | -    |      |
| t <sub>d(on)</sub>  | Turn-on Delay Time                                     | V <sub>DD</sub> =100V, R <sub>G</sub> =25Ω, I <sub>D</sub> =18A  | -    | 24   | -    | ns   |
| t <sub>r</sub>      | Turn-on Rise Time                                      |                                                                  | -    | 45   | -    |      |
| t <sub>d(off)</sub> | Turn-off Delay Time                                    |                                                                  | -    | 101  | -    |      |
| t <sub>f</sub>      | Turn-off Fall Time                                     |                                                                  | -    | 95   | -    |      |
| I <sub>S</sub>      | Continuous Source Current                              | T <sub>C</sub> =25°C                                             | -    | -    | 18   | A    |
| I <sub>SM</sub>     | Pulsed Diode Forward Current                           |                                                                  | -    | -    | 72   |      |
| V <sub>SD</sub>     | Diode Forward Voltage                                  | T <sub>J</sub> =25°C, I <sub>SD</sub> =18A, V <sub>GS</sub> =0V  | -    | -    | 1.4  | V    |
| t <sub>rr</sub>     | Body Diode Reverse Recovery Time                       | V <sub>GS</sub> =0V, I <sub>S</sub> =18A, diF/dt=100A/μs         | -    | 230  | -    | ns   |
| Q <sub>rr</sub>     | Body Diode Reverse Recovery Charge                     |                                                                  | -    | 1.8  | -    | μC   |

### Notes:

- 1、The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、The EAS data shows Max. rating. I<sub>AS</sub>=15A, V<sub>DD</sub>=50V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C
- 3、The test condition is Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

## 4. Typical Characteristics

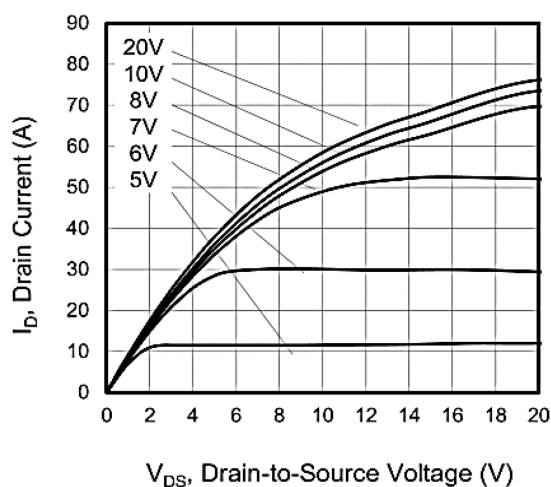


Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )

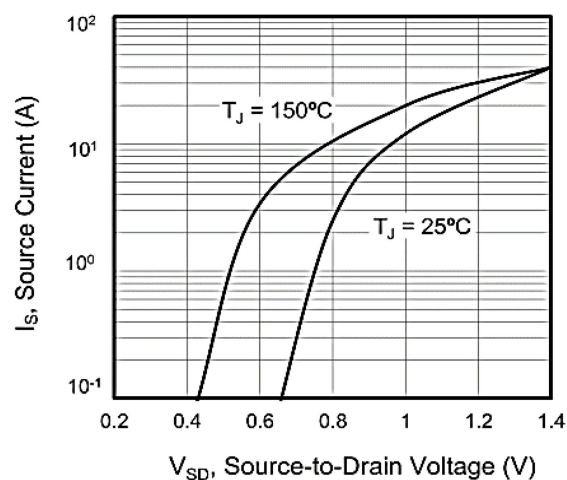


Figure 2. Body Diode Forward Voltage

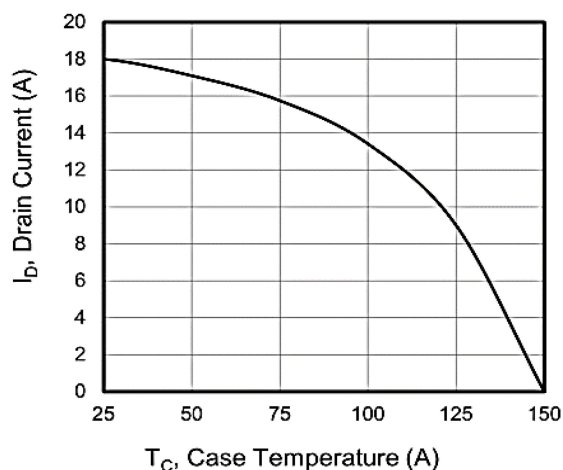


Figure 3. Drain Current vs. Temperature

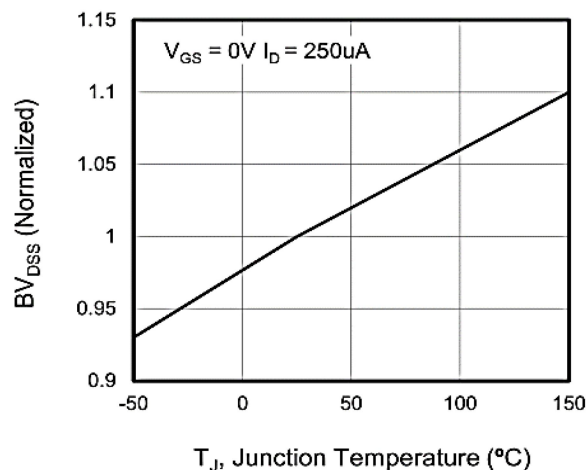


Figure 4.  $BV_{DS}$  Variation vs. Temperature

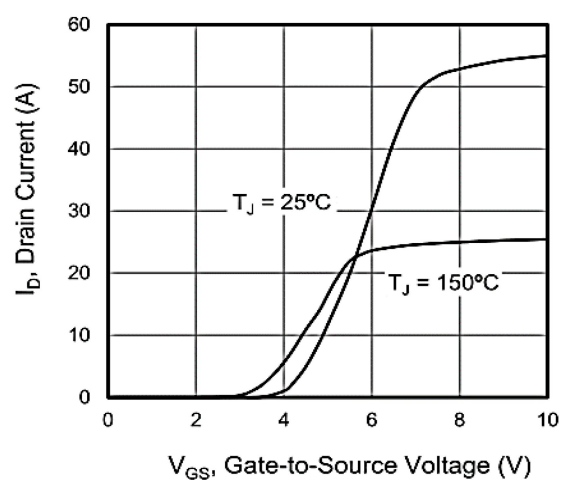


Figure 5. Transfer Characteristics

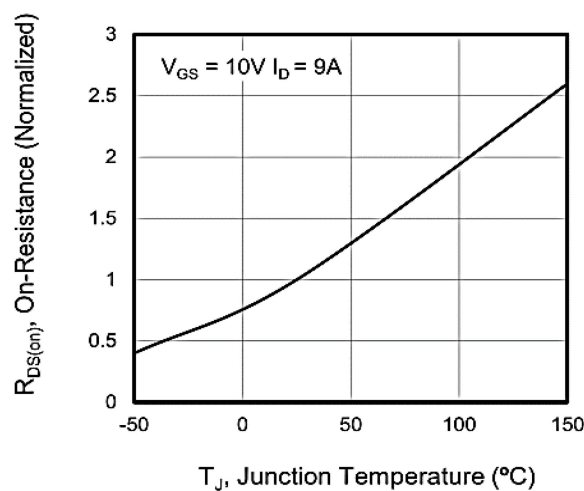


Figure 6. On-Resistance vs. Temperature

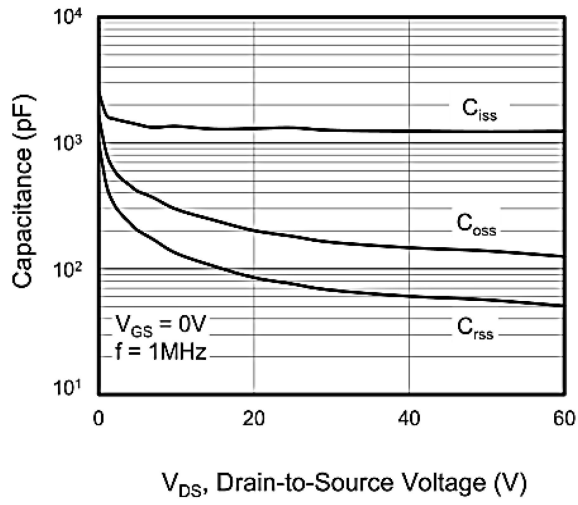


Figure 7. Capacitance

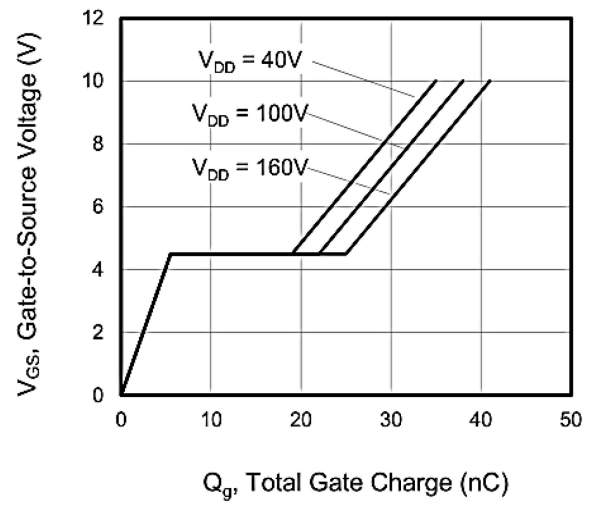


Figure 8. Gate Charge

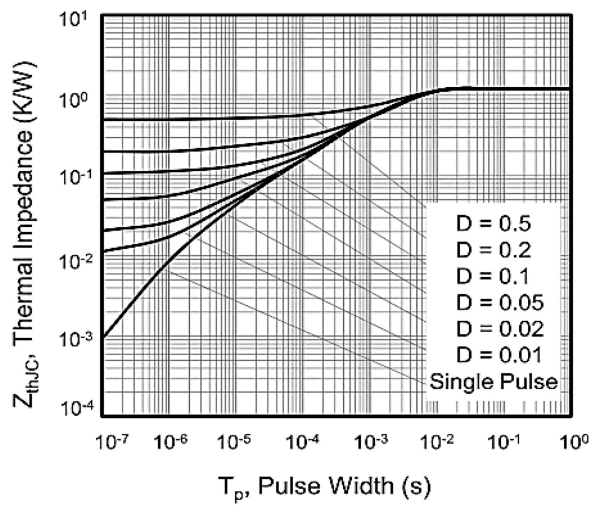
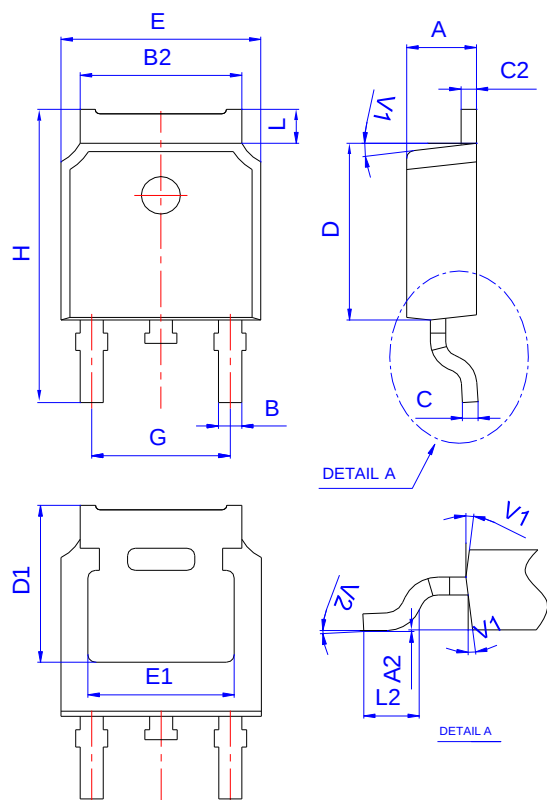


Figure 10. Transient Thermal Impedance

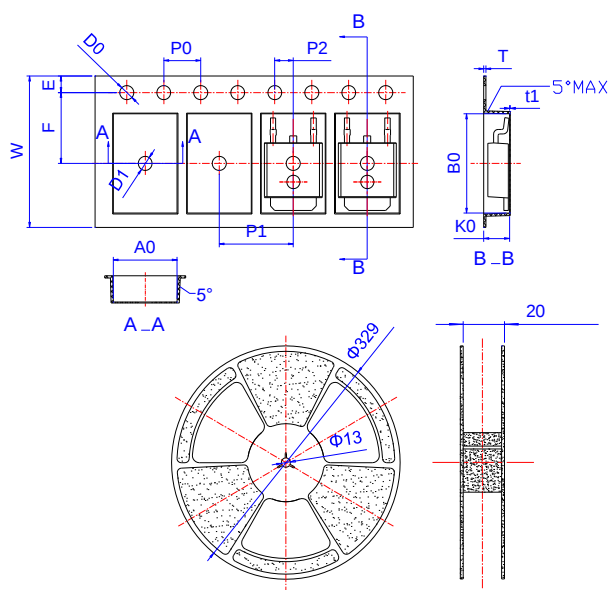
## 4.Package Mechanical Data

## TO-252 Package



| Ref. | Dimensions  |      |       |          |      |       |
|------|-------------|------|-------|----------|------|-------|
|      | Millimeters |      |       | Inches   |      |       |
|      | Min.        | Typ. | Max.  | Min.     | Typ. | Max.  |
| A    | 2.10        |      | 2.50  | 0.083    |      | 0.098 |
| A2   | 0.00        |      | 0.10  | 0        |      | 0.004 |
| B    | 0.66        |      | 0.86  | 0.026    |      | 0.034 |
| B2   | 5.18        |      | 5.48  | 0.202    |      | 0.216 |
| C    | 0.40        |      | 0.60  | 0.016    |      | 0.024 |
| C2   | 0.44        |      | 0.58  | 0.017    |      | 0.023 |
| D    | 5.90        |      | 6.30  | 0.232    |      | 0.248 |
| D1   | 5.30REF     |      |       | 0.209REF |      |       |
| E    | 6.40        |      | 6.80  | 0.252    |      | 0.268 |
| E1   | 4.63        |      |       | 0.182    |      |       |
| G    | 4.47        |      | 4.67  | 0.176    |      | 0.184 |
| H    | 9.50        |      | 10.70 | 0.374    |      | 0.421 |
| L    | 1.09        |      | 1.21  | 0.043    |      | 0.048 |
| L2   | 1.35        |      | 1.65  | 0.053    |      | 0.065 |
| V1   |             | 7°   |       |          | 7°   |       |
| V2   | 0°          |      | 6°    | 0°       |      | 6°    |

## Reel Specification-TO-252



| Ref. | Dimensions  |      |      |        |       |       |
|------|-------------|------|------|--------|-------|-------|
|      | Millimeters |      |      | Inches |       |       |
|      | Min.        | Typ. | Max. | Min.   | Typ.  | Max.  |
| W    | 15.9        | 16   | 16.1 | 0.626  | 0.630 | 0.634 |
| E    | 1.65        | 1.75 | 1.85 | 0.065  | 0.069 | 0.073 |
| F    | 7.4         | 7.5  | 7.6  | 0.291  | 0.295 | 0.299 |
| D0   | 1.4         | 1.5  | 1.6  | 0.055  | 0.059 | 0.063 |
| D1   | 1.4         | 1.5  | 1.6  | 0.055  | 0.059 | 0.063 |
| P0   | 3.9         | 4    | 4.1  | 0.154  | 0.157 | 0.161 |
| P1   | 7.9         | 8    | 8.1  | 0.311  | 0.315 | 0.319 |
| P2   | 1.9         | 2    | 2.1  | 0.075  | 0.079 | 0.083 |
| A0   | 6.85        | 6.9  | 7    | 0.270  | 0.271 | 0.276 |
| B0   | 10.45       | 10.5 | 10.6 | 0.411  | 0.413 | 0.417 |
| K0   | 2.68        | 2.78 | 2.88 | 0.105  | 0.109 | 0.113 |
| T    | 0.24        |      | 0.27 | 0.009  |       | 0.011 |
| t1   | 0.10        |      |      | 0.004  |       |       |
| 10P0 | 39.8        | 40   | 40.2 | 1.567  | 1.575 | 1.583 |